



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.: 10/780,030 Confirmation No.: 9259
First Named Inventor: Park, Jongmin Filing Date: 17 February 2004
Group Art Unit: 2827 Examiner: Lam, David
Atty. Docket No.: R-0004 US
Title: Voltage Discharge Technique for Controlling Threshold-voltage Characteristics of Floating-gate Transistor in Circuitry Such as Flash EPROM
Assignee(s): ProMOS Technologies Inc.

Mountain View, California
26 April 2005

COMMISSIONER FOR PATENTS
PO Box 1450
Alexandria, Virginia 22313-1450

PRELIMINARY AMENDMENT TO DRAWINGS

Sir:

The drawings for the above patent application should be amended as follows:

In Fig. 4, the lead line for reference symbol V_{BEH} should be changed to an arrow; the lead line for reference symbol V_{CEL} should be changed to an arrow; a short horizontal line should be added along the vertical axis to the right of reference symbol V_{DD} for the V_{EO} curve; reference symbol " V_{DD} " should be added to the immediate left of the vertical axis between reference symbol V_{BEH} and directly underlying reference symbol V_{SS} at a distance above reference symbol V_{SS} approximately equal to the distance between reference symbols V_{SS} and V_{DD} to the left of the vertical axis for the V_{IT} curve; and a short horizontal line should be added along the vertical axis to the right of newly added reference symbol V_{DD} .

Enclosed is a copy of the relevant drawing sheet in which the foregoing changes are indicated in red.

Ronald J. Meetin
Attorney at Law
210 Central Avenue
Mountain View, CA
94043-4869

Tel.: 650-964-9767
Fax: 650-964-9779